

# PUMH9-Q

# 50 V, 100 mA NPN/NPN resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

7 October 2021

**Product data sheet** 

### 1. General description

NPN/NPN Resistor-Equipped double Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: PUMB9-Q NPN/PNP complement: PUMD9-Q

#### 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

### 3. Applications

- · Digital application in automotive and industrial segments
- · Cost-saving alternative for BC847-Q series in digital applications
- Controlling IC inputs
- · Switching loads

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	100	mA
R1	bias resistor 1		[1]	7	10	13	kΩ
R2/R1	bias resistor ratio		[1]	3.7	4.7	5.7	

[1] See "Section 11: Test information" for resistor calculation and test conditions.



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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1
6	01	output (collector) TR1	□1 □2 □3	
			TSSOP6 (SOT363)	
				GND1 I1 O2 sym063

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package	nge					
	Name	Description	Version				
PUMH9-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363				

## 7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMH9-Q	Н%9

[1] % = placeholder for manufacturing site code

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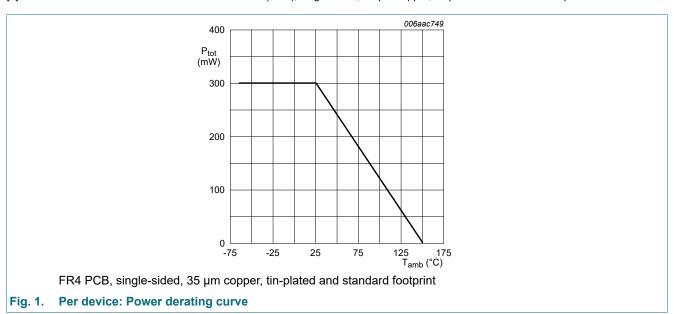
# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or					
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	6	V
VI	input voltage	positive		-	40	V
		negative		-	-6	V
Io	output current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
Per device						'
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

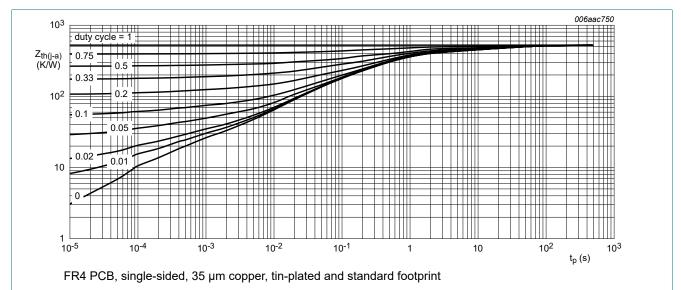


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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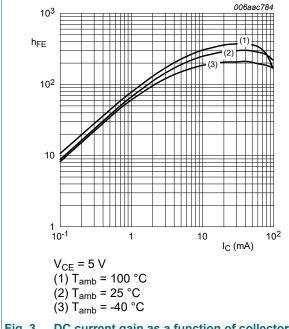
### 10. Characteristics

#### **Table 7. Characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
$V_{(BR)CBO}$	collector-base breakdown voltage	I <sub>C</sub> = 100 μA; I <sub>E</sub> = 0 A		50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}$		50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A		-	-	100	nA
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A		-	-	150	μΑ
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA		100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 5 mA; I <sub>B</sub> = 0.25 mA		-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA		-	0.7	0.5	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 1 mA		1.4	0.8	-	V
R1	bias resistor 1		[1]	7	10	13	kΩ
R2/R1	bias resistor ratio		[1]	3.7	4.7	5.7	
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz		-	-	2.5	pF
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; f = 100 MHz	[2]	-	230	-	MHz

- [1] See "Section 11: Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor



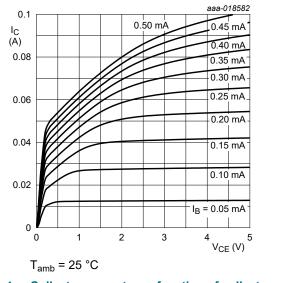
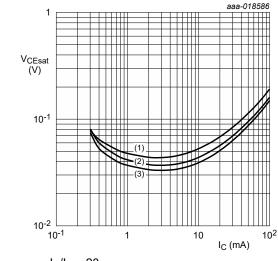


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

Fig. 3. DC current gain as a function of collector current; typical values

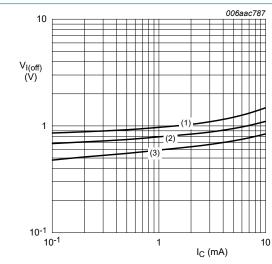
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 $I_{\rm C}/I_{\rm B} = 20$ 

(1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

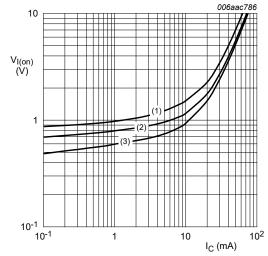


 $V_{CE} = 5 V$ 

(1)  $T_{amb} = -40 \,^{\circ}\text{C}$ (2)  $T_{amb} = 25 \,^{\circ}\text{C}$ 

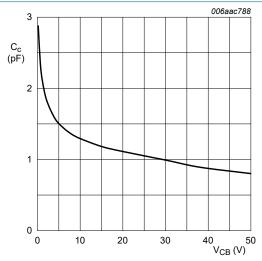
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 7. Off-state input voltage as a function of collector current; typical values



V<sub>CE</sub> = 0.3 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 6. On-state input voltage as a function of collector current; typical values

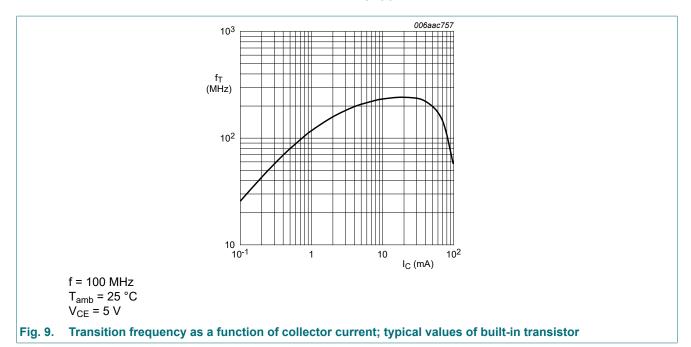


f = 1 MHz

T<sub>amb</sub> = 25 °C

Fig. 8. Collector capacitance as a function of collectorbase voltage; typical values

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### 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

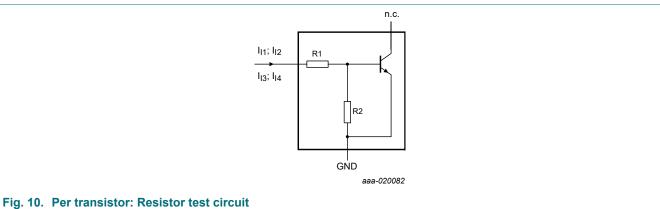
#### **Resistor calculation**

• Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$



#### - I or translator: Recipies tool circuit

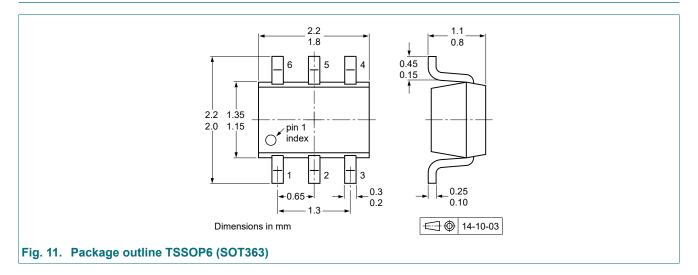
#### Resistor test conditions

**Table 8. Resistor test conditions** 

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I <sub>11</sub>	I <sub>I2</sub>	I <sub>13</sub>	I <sub>14</sub>	
Per transistor							
PUMH9-Q	10	47	90 μΑ	140 μΑ	-55 μΑ	-105 μA	

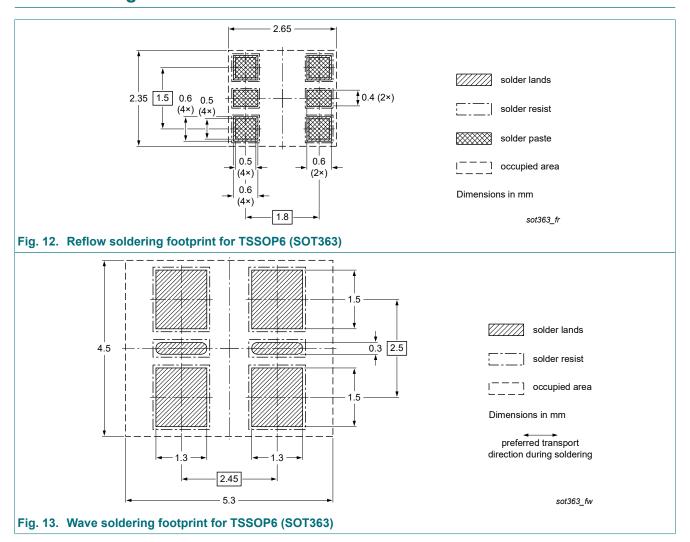
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# 12. Package outline



50 V, 100 mA NPN/NPN resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

# 13. Soldering



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# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMH9-Q v.2	20211007	Product data sheet	-	PUMH9-Q v.1
Modification:	<ul> <li>Pinning: Graphic</li> <li>Limiting values: d</li> <li>Characteristics: I<sub>0</sub></li> <li>Characteristics: r</li> <li>Characteristics: L</li> <li>Characteristics: V</li> </ul>	on: added new lines at the	100 nA 85 with aaa-018586 tions	and resistor test condition
PUMH9-Q v.1	20210625	Product data sheet	-	-

#### 50 V, 100 mA NPN/NPN resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PUMH9-Q

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